

UT2302

Power MOSFET

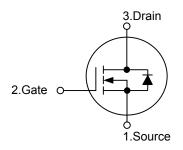
N-CHANNEL ENHANCEMENT MODE

DESCRIPTION

The UTC **UT2302** is N-channel Power MOSFET, designed with high density cell, with fast switching speed, ultra low on-resistance, and excellent thermal and electrical capabilities.

Used in commercial and industrial surface mount applications and suited for low voltage applications such as DC/DC converters.

SYMBOL



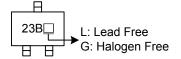
3 2 1 SOT-23 3 2 1 SOT-23-3 (JEDEC TO-236)

ORDERING INFORMATION

Ordering Number		Dookago	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UT2302L-AE2-R	UT2302G-AE2-R	SOT-23-3	S	G	D	Tape Reel	
UT2302L-AE3-R	UT2302G-AE3-R	SOT-23	S	G	D	Tape Reel	

UT2302L-AE3-R (1)Packing Type (2)Package Type (3)Lead Free	(1) R: Tape Reel (2) AE2: SOT-23-3, AE3: SOT-23 (3) G: Halogen Free, L: Lead Free
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MARKING



UT2302

■ ABSOLUTE MAXIMUM RATINGS (Ta = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V _{DSS}	20	V
Gate-Source Voltage		V _{GSS}	±8	V
	Continuous	I _D	2.4	A
Drain Current (Note 1)	Pulsed	I _{DM}	2.4 10	
Power Dissipation		PD	1.25	W
Junction Temperature		TJ	+150	°C
Storage Temperature		T _{STG}	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

THERMAL DATA

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT
Junction to Ambient (Note 3)	θ_{JA}			100	°C/W

■ ELECTRICAL CHARACTERISTICS (Ta =25°C, unless otherwise specified)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT			
OFF CHARACTERISTICS								
BV _{DSS}	V _{GS} =0 V, I _D =250 μA	20			V			
I _{DSS}	V _{DS} =20 V, V _{GS} =0 V			1.0	μA			
I _{GSS}	V_{DS} =0 V, V_{GS} = ±8V			±100	nA			
ON CHARACTERISTICS								
V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250 μA	0.45			V			
Б	V _{GS} =4.5 V, I _D =7.2 A			50	mΩ			
nds(on)	V _{GS} =2.5 V, I _D =3.1 A		75	95	mΩ			
I _{D(ON)}	$V_{DS} \ge 5V, V_{GS} = 4.5 V$	6			Α			
CISS			450		pF			
C _{OSS}	V _{DS} =10 V, V _{GS} =0V, f=1MHz		70		pF			
C _{RSS}			43		pF			
t _{D(ON)}			7	15	ns			
t _R	V_{DD} =10V, R _L =10 Ω, I _D =1A, V _{GEN} =4.5V, R _G =6Ω		55	80	ns			
t _{D(OFF)}			16	60	ns			
t _F			10	25	ns			
Q_G			5.2	10	nC			
Q_{GS}	V _{DS} =10V, V _{GS} =4.5 V, I _D =3.6 A		0.65		nC			
Q_{GD}			1.5		nC			
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS								
V_{SD}	V _{GS} =0 V, I _S =1.0 A		0.76	1.2	V			
				16	^			
IS				1.0	A			
	BV_{DSS} I_{DSS} I_{GSS} $V_{GS(TH)}$ $R_{DS(ON)}$ $I_{D(ON)}$ C_{ISS} C_{OSS} C_{RSS} $t_{D(OFF)}$ t_{F} Q_{G} Q_{GS} Q_{GD} STICS AND	$\begin{array}{ c c c c c c c c c c c c c c c c c c c$	$\begin{array}{ c c c c c c c c c c c c c c c c c c c$	$\begin{array}{ c c c c c c c c c c c c c c c c c c c$	$\begin{array}{ c c c c c c c c c c c c c c c c c c c$			

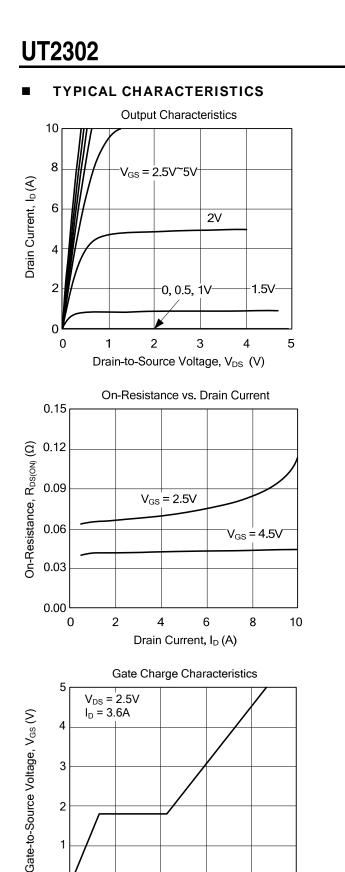
Note:1. Repetitive Rating: Pulse width limited by $T_{\rm J}$

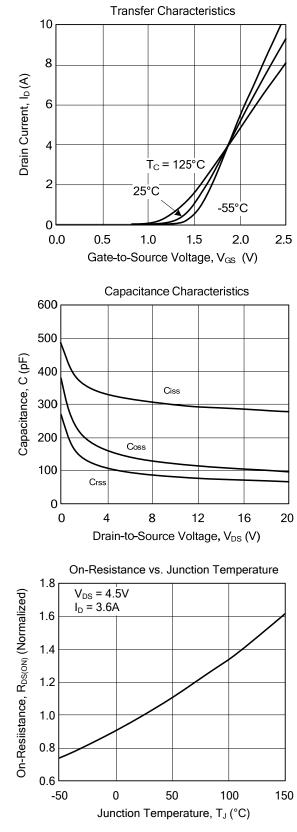
2. Pulse Test: Pulse width \leq 300µs, Duty cycle \leq 2%

3. Surface mounted on 1 in² copper pad of FR4 board



Power MOSFET

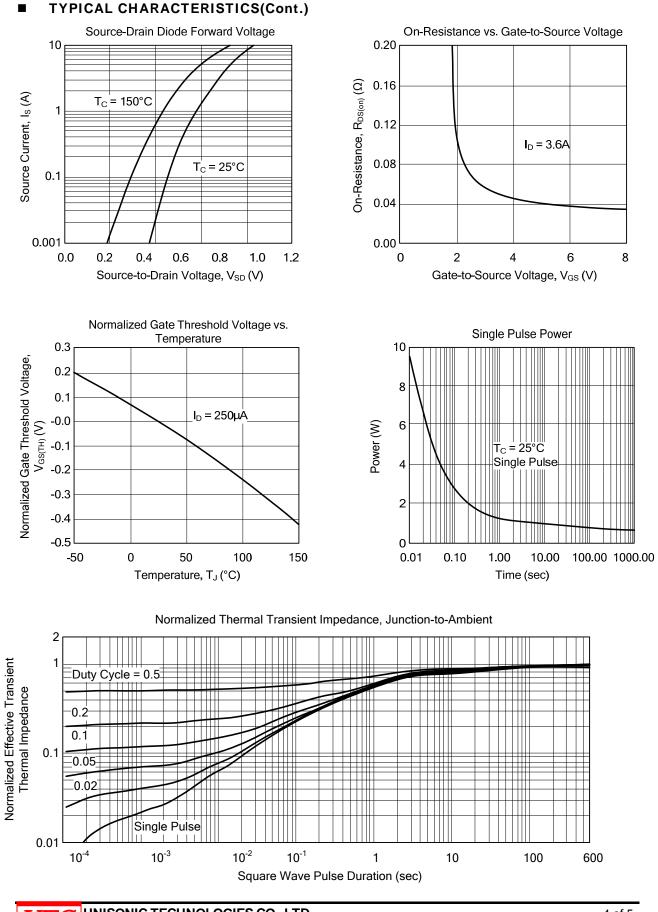






Total Gate Charge, Qg (nC)

UT2302



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